

# Ivan G Ivanov

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

205  
papers

3,380  
citations

31  
h-index

48  
g-index

214  
ext. papers

3,800  
ext. citations

3.1  
avg, IF

4.98  
L-index

#	Paper	IF	Citations
205	Bidirectional Hydrogen Electrocatalysis on Epitaxial Graphene.. <i>ACS Omega</i> , <b>2022</b> , 7, 13221-13227	3.9	1
204	Silver nanoparticle array on weakly interacting epitaxial graphene substrate as catalyst for hydrogen evolution reaction under neutral conditions. <i>Applied Physics Letters</i> , <b>2021</b> , 119, 153902	3.4	1
203	Exploring the Interface Landscape of Noble Metals on Epitaxial Graphene. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2021</b> , 218, 2000673	1.6	4
202	Charge state control of the silicon vacancy and divacancy in silicon carbide. <i>Journal of Applied Physics</i> , <b>2021</b> , 129, 215702	2.5	4
201	MOCVD of AlN on epitaxial graphene at extreme temperatures. <i>CrystEngComm</i> , <b>2021</b> , 23, 385-390	3.3	6
200	Resolving mobility anisotropy in quasi-free-standing epitaxial graphene by terahertz optical Hall effect. <i>Carbon</i> , <b>2021</b> , 172, 248-259	10.4	3
199	Critical View on Buffer Layer Formation and Monolayer Graphene Properties in High-Temperature Sublimation. <i>Applied Sciences (Switzerland)</i> , <b>2021</b> , 11, 1891	2.6	0
198	Deep levels related to the carbon antisite-vacancy pair in 4H-SiC. <i>Journal of Applied Physics</i> , <b>2021</b> , 130, 065703	2.5	3
197	Study of Cucurbit[7]uril nanocoating on epitaxial graphene to design a versatile sensing platform. <i>Applied Surface Science</i> , <b>2021</b> , 563, 150096	6.7	0
196	Clustering and Morphology Evolution of Gold on Nanostructured Surfaces of Silicon Carbide: Implications for Catalysis and Sensing. <i>ACS Applied Nano Materials</i> , <b>2021</b> , 4, 1282-1293	5.6	4
195	Reactive sputtering of CS <sub>x</sub> thin solid films using CS <sub>2</sub> as precursor. <i>Vacuum</i> , <b>2020</b> , 182, 109775	3.7	6
194	Developing silicon carbide for quantum spintronics. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 190501	3.4	45
193	Epitaxial Graphene Growth on the Step-Structured Surface of Off-Axis C-Face 3C-SiC(1111). <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 1900718	1.3	1
192	A patterning-free approach for growth of free-standing graphene nanoribbons using step-bunched facets of off-oriented 4H-SiC(0 0 0 1) epilayers. <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 115102	3	1
191	Excitonic emission in heavily Ga-doped zinc oxide films grown on GaN. <i>Journal of Luminescence</i> , <b>2020</b> , 223, 117265	3.8	4
190	In Situ Activation of an Indium(III) Triazenide Precursor for Epitaxial Growth of Indium Nitride by Atomic Layer Deposition. <i>Chemistry of Materials</i> , <b>2020</b> , 32, 4481-4489	9.6	15
189	Spin-relaxation times exceeding seconds for color centers with strong spin-orbit coupling in SiC. <i>New Journal of Physics</i> , <b>2020</b> , 22, 103051	2.9	7

188	Surface functionalization of epitaxial graphene using ion implantation for sensing and optical applications. <i>Carbon</i> , <b>2020</b> , 157, 169-184	10.4	8
187	Interplay between thin silver films and epitaxial graphene. <i>Surface and Coatings Technology</i> , <b>2020</b> , 381, 125200	4.4	6
186	Nanoscale phenomena ruling deposition and intercalation of AlN at the graphene/SiC interface. <i>Nanoscale</i> , <b>2020</b> , 12, 19470-19476	7.7	28
185	Direct epitaxial nanometer-thin InN of high structural quality on 4H-SiC by atomic layer deposition. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 093101	3.4	5
184	Manipulation of epitaxial graphene towards novel properties and applications. <i>Materials Today: Proceedings</i> , <b>2020</b> , 20, 37-45	1.4	2
183	Probing the uniformity of silver-doped epitaxial graphene by micro-Raman mapping. <i>Physica B: Condensed Matter</i> , <b>2020</b> , 580, 411751	2.8	6
182	Electrical Charge State Manipulation of Single Silicon Vacancies in a Silicon Carbide Quantum Optoelectronic Device. <i>Nano Letters</i> , <b>2019</b> , 19, 7173-7180	11.5	36
181	The Endocyclic Carbon Substituent of Guanidinate and Amidinate Precursors Controlling Atomic Layer Deposition of InN Films. <i>Journal of Physical Chemistry C</i> , <b>2019</b> , 123, 25691-25700	3.8	13
180	A comparative study of high-quality C-face and Si-face 3C-SiC(1 1 1) grown on off-oriented 4H-SiC substrates. <i>Journal Physics D: Applied Physics</i> , <b>2019</b> , 52, 345103	3	7
179	Energy levels and charge state control of the carbon antisite-vacancy defect in 4H-SiC. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 212105	3.4	11
178	Seed-Layer-Free Atomic Layer Deposition of Highly Uniform Al <sub>2</sub> O <sub>3</sub> Thin Films onto Monolayer Epitaxial Graphene on Silicon Carbide. <i>Advanced Materials Interfaces</i> , <b>2019</b> , 6, 1900097	4.6	15
177	Effect of epitaxial graphene morphology on adsorption of ambient species. <i>Applied Surface Science</i> , <b>2019</b> , 486, 239-248	6.7	10
176	High-fidelity spin and optical control of single silicon-vacancy centres in silicon carbide. <i>Nature Communications</i> , <b>2019</b> , 10, 1954	17.4	99
175	Anodization study of epitaxial graphene: insights on the oxygen evolution reaction of graphitic materials. <i>Nanotechnology</i> , <b>2019</b> , 30, 285701	3.4	1
174	Atomic layer deposition of InN using trimethylindium and ammonia plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2019</b> , 37, 020926	2.9	18
173	Ligand hyperfine interactions at silicon vacancies in 4H-SiC. <i>Journal of Physics Condensed Matter</i> , <b>2019</b> , 31, 195501	1.8	9
172	Probing the uniformity of hydrogen intercalation in quasi-free-standing epitaxial graphene on SiC by micro-Raman mapping and conductive atomic force microscopy. <i>Nanotechnology</i> , <b>2019</b> , 30, 284003	3.4	16
171	Real-time sensing of lead with epitaxial graphene-integrated microfluidic devices. <i>Sensors and Actuators B: Chemical</i> , <b>2019</b> , 288, 425-431	8.5	26

170	Raman probing of hydrogen-intercalated graphene on Si-face 4H-SiC. <i>Materials Science in Semiconductor Processing</i> , <b>2019</b> , 96, 145-152	4.3	16
169	Bioelectrocatalysis on Anodized Epitaxial Graphene and Conventional Graphitic Interfaces. <i>ChemElectroChem</i> , <b>2019</b> , 6, 3791-3796	4.3	1
168	CVD growth and properties of on-axis vanadium doped semi-insulating 4H-SiC epilayers. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 045702	2.5	6
167	First-Principles Study on Photoluminescence Quenching of Divacancy in 4H SiC. <i>Materials Science Forum</i> , <b>2019</b> , 963, 714-717	0.4	1
166	Silicon carbonitride thin films deposited by reactive high power impulse magnetron sputtering. <i>Surface and Coatings Technology</i> , <b>2018</b> , 335, 248-256	4.4	9
165	Quantum Properties of Dichroic Silicon Vacancies in Silicon Carbide. <i>Physical Review Applied</i> , <b>2018</b> , 9,	4.3	65
164	Defects in silicon carbide grown by fluorinated chemical vapor deposition chemistry. <i>Physica B: Condensed Matter</i> , <b>2018</b> , 535, 44-49	2.8	1
163	Performance tuning of gas sensors based on epitaxial graphene on silicon carbide. <i>Materials and Design</i> , <b>2018</b> , 153, 153-158	8.1	19
162	Elimination of step bunching in the growth of large-area monolayer and multilayer graphene on off-axis 3C SiC (111). <i>Carbon</i> , <b>2018</b> , 140, 533-542	10.4	12
161	Iron Oxide Nanoparticle Decorated Graphene for Ultra-Sensitive Detection of Volatile Organic Compounds. <i>Proceedings (mdpi)</i> , <b>2018</b> , 2, 985	0.3	1
160	Understanding Graphene Response to Neutral and Charged Lead Species: Theory and Experiment. <i>Materials</i> , <b>2018</b> , 11,	3.5	9
159	Excitation properties of the divacancy in 4H-SiC. <i>Physical Review B</i> , <b>2018</b> , 98,	3.3	33
158	Identification and tunable optical coherent control of transition-metal spins in silicon carbide. <i>Npj Quantum Information</i> , <b>2018</b> , 4,	8.6	35
157	Lead (Pb) interfacing with epitaxial graphene. <i>Physical Chemistry Chemical Physics</i> , <b>2018</b> , 20, 17105-17116	6.6	14
156	Surface functionalization of epitaxial graphene on SiC by ion irradiation for gas sensing application. <i>Applied Surface Science</i> , <b>2017</b> , 403, 707-716	6.7	19
155	Multi-scale investigation of interface properties, stacking order and decoupling of few layer graphene on C-face 4H-SiC. <i>Carbon</i> , <b>2017</b> , 116, 722-732	10.4	21
154	Experimental study of the effect of local atomic ordering on the energy band gap of melt grown InGaAsN alloys. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 085005	1.8	10
153	Rolling performance of carbon nitride-coated bearing components in different lubrication regimes. <i>Tribology International</i> , <b>2017</b> , 114, 141-151	4.9	16

152	Monitoring of epitaxial graphene anodization. <i>Electrochimica Acta</i> , <b>2017</b> , 238, 91-98	6.7	16
151	Calibration on wide-ranging aluminum doping concentrations by photoluminescence in high-quality uncompensated p-type 4H-SiC. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 072101	3.4	7
150	In-situ terahertz optical Hall effect measurements of ambient effects on free charge carrier properties of epitaxial graphene. <i>Scientific Reports</i> , <b>2017</b> , 7, 5151	4.9	16
149	Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. <i>ECS Journal of Solid State Science and Technology</i> , <b>2017</b> , 6, P741-P745	2	
148	(Invited) Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. <i>ECS Transactions</i> , <b>2017</b> , 80, 107-115	1	
147	Optical properties of thick GaInAs(Sb)N layers grown by liquid-phase epitaxy. <i>Journal of Physics: Conference Series</i> , <b>2017</b> , 794, 012013	0.3	4
146	Chloride-based SiC growth on a-axis 4H-SiC substrates. <i>Physica B: Condensed Matter</i> , <b>2016</b> , 480, 23-25	2.8	1
145	Surface photovoltage and photoluminescence study of thick Ga(In)AsN layers grown by liquid-phase epitaxy. <i>Journal of Physics: Conference Series</i> , <b>2016</b> , 700, 012028	0.3	8
144	Trimethylboron as Single-Source Precursor for Boron-Carbon Thin Film Synthesis by Plasma Chemical Vapor Deposition. <i>Journal of Physical Chemistry C</i> , <b>2016</b> , 120, 21990-21997	3.8	9
143	Modified Epitaxial Graphene on SiC for Extremely Sensitive and Selective Gas Sensors. <i>Materials Science Forum</i> , <b>2016</b> , 858, 1145-1148	0.4	8
142	Light emission enhancement from ZnO nanostructured films grown on Gr/SiC substrates. <i>Carbon</i> , <b>2016</b> , 99, 295-301	10.4	6
141	A comparative study of direct current magnetron sputtering and high power impulse magnetron sputtering processes for CN <sub>x</sub> thin film growth with different inert gases. <i>Diamond and Related Materials</i> , <b>2016</b> , 64, 13-26	3.5	18
140	Growth optimization and applicability of thick on-axis SiC layers using sublimation epitaxy in vacuum. <i>Journal of Crystal Growth</i> , <b>2016</b> , 448, 51-57	1.6	3
139	Surface engineering of SiC via sublimation etching. <i>Applied Surface Science</i> , <b>2016</b> , 390, 816-822	6.7	8
138	Single Domain 3C-SiC Growth on Off-Oriented 4H-SiC Substrates. <i>Crystal Growth and Design</i> , <b>2015</b> , 15, 2940-2947	3.5	31
137	Graphene self-switching diodes as zero-bias microwave detectors. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 093116	3.4	23
136	Low-temperature growth of low friction wear-resistant amorphous carbon nitride thin films by mid-frequency, high power impulse, and direct current magnetron sputtering. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2015</b> , 33, 05E112	2.9	11
135	Quasi-free-standing monolayer and bilayer graphene growth on homoepitaxial on-axis 4H-SiC(0 0 0 1) layers. <i>Carbon</i> , <b>2015</b> , 82, 12-23	10.4	16

134	Optical properties and Zeeman spectroscopy of niobium in silicon carbide. <i>Physical Review B</i> , <b>2015</b> , 92,	3.3	5
133	Wafer-scale epitaxial graphene on SiC for sensing applications <b>2015</b> ,		2
132	Brominated Chemistry for Chemical Vapor Deposition of Electronic Grade SiC. <i>Chemistry of Materials</i> , <b>2015</b> , 27, 793-801	9.6	7
131	Assessment of H-intercalated graphene for microwave FETs through material characterization and electron transport studies. <i>Carbon</i> , <b>2015</b> , 81, 96-104	10.4	6
130	On the use of methane as a carbon precursor in Chemical Vapor Deposition of silicon carbide. <i>Journal of Crystal Growth</i> , <b>2014</b> , 390, 24-29	1.6	12
129	Layer-number determination in graphene on SiC by reflectance mapping. <i>Carbon</i> , <b>2014</b> , 77, 492-500	10.4	46
128	Hydrogen at zinc vacancy of ZnO: An EPR and ESEEM study <b>2014</b> ,		4
127	Stable and metastable Si negative-U centers in AlGaN and AlN. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 162106	3.4	41
126	Lateral Enlargement Growth Mechanism of 3C-SiC on Off-Oriented 4H-SiC Substrates. <i>Crystal Growth and Design</i> , <b>2014</b> , 14, 6514-6520	3.5	37
125	Resonant ionization of shallow donors in electric field. <i>Physica Scripta</i> , <b>2014</b> , 89, 085802	2.6	
124	High-Resolution Raman and Luminescence Spectroscopy of Isotope-Pure $^{28}\text{Si}^{12}\text{C}$ , Natural and $^{13}\text{C}$ Enriched 4H-SiC. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 471-474	0.4	9
123	Reactive high power impulse magnetron sputtering of CF <sub>x</sub> thin films in mixed Ar/CF <sub>4</sub> and Ar/C <sub>4</sub> F <sub>8</sub> discharges. <i>Thin Solid Films</i> , <b>2013</b> , 542, 21-30	2.2	14
122	Process stability and morphology optimization of very thick 4H-SiC epitaxial layers grown by chloride-based CVD. <i>Journal of Crystal Growth</i> , <b>2013</b> , 380, 55-60	1.6	14
121	Negative-U behavior of the Si donor in Al <sub>0.77</sub> Ga <sub>0.23</sub> N. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 042101	3.4	8
120	Reduction of structural defects in thick 4H-SiC epitaxial layers grown on 4° off-axis substrates. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 223502	2.5	23
119	Defects in N, O and N, Zn implanted ZnO bulk crystals. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 103509	2.5	31
118	Optical Properties of the Niobium Centre in 4H, 6H, and 15R SiC. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 405-408	0.4	1
117	Morphology Optimization of Very Thick 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 251-254	0.4	

116	Photoluminescence of 8H-SiC. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 347-350	0.4	1
115	Magnetic resonance identification of hydrogen at a zinc vacancy in ZnO. <i>Journal of Physics Condensed Matter</i> , <b>2013</b> , 25, 335804	1.8	12
114	Optical identification and electronic configuration of tungsten in 4H- and 6H-SiC. <i>Physica B: Condensed Matter</i> , <b>2012</b> , 407, 1462-1466	2.8	12
113	Considerably long carrier lifetimes in high-quality 3C-SiC(111). <i>Applied Physics Letters</i> , <b>2012</b> , 100, 252101	3.4	25
112	Investigation of Intrinsic Carbon-Related Defects in 4H-SiC by Selective-Excitation Photoluminescence Spectroscopy. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 259-262	0.4	1
111	Control of Epitaxial Graphene Thickness on 4H-SiC(0001) and Buffer Layer Removal through Hydrogen Intercalation. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 605-608	0.4	8
110	Electronic Configuration of Tungsten in 4H-, 6H-, and 15R-SiC. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 211-216	0.4	
109	CFx thin solid films deposited by high power impulse magnetron sputtering: Synthesis and characterization. <i>Surface and Coatings Technology</i> , <b>2011</b> , 206, 646-653	4.4	34
108	Splitting of type-I (N-B, P-Al) and type-II (N-Al, N-Ga) donor-acceptor pair spectra in 3C-SiC. <i>Physical Review B</i> , <b>2011</b> , 83,	3.3	3
107	A SIMS study on Mg diffusion in Zn <sub>0.94</sub> Mg <sub>0.06</sub> O/ZnO heterostructures grown by metal organic chemical vapor deposition. <i>Applied Surface Science</i> , <b>2011</b> , 257, 8629-8633	6.7	12
106	Donor-Acceptor Pair Luminescence of P-Al and N-Al Pairs in 3C-SiC and the Ionization Energy of the P Donor. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 245-248	0.4	
105	Ionization energy of the phosphorus donor in 3C-SiC from the donor-acceptor pair emission. <i>Journal of Applied Physics</i> , <b>2010</b> , 108, 063532	2.5	5
104	EPR and ENDOR Studies of Shallow Donors in SiC. <i>Applied Magnetic Resonance</i> , <b>2010</b> , 39, 49-85	0.8	9
103	In-grown stacking faults in 4H-SiC epilayers grown on off-cut substrates. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 123513	2.5	25
102	Temperature Dependence and Selective Excitation of the Phosphorus Related Photoluminescence in 4H-SiC. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 263-266	0.4	
101	Annealing effects on optical properties of low temperature grown ZnO nanorod arrays. <i>Journal of Applied Physics</i> , <b>2009</b> , 105, 053503	2.5	116
100	Wave-Function Symmetry and the Properties of Shallow P Donors in 4H SiC. <i>Materials Science Forum</i> , <b>2008</b> , 600-603, 445-448	0.4	1
99	Common point defects in as-grown ZnO substrates studied by optical detection of magnetic resonance. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 1006-1009	1.6	4

98	Magnetic resonance studies of defects in electron-irradiated ZnO substrates. <i>Physica B: Condensed Matter</i> , <b>2007</b> , 401-402, 507-510	2.8	2
97	Uniform hot-wall MOCVD epitaxial growth of 2 inch AlGaIn/GaN HEMT structures. <i>Journal of Crystal Growth</i> , <b>2007</b> , 300, 100-103	1.6	24
96	Recombination centers in as-grown and electron-irradiated ZnO substrates. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 093504	2.5	17
95	Theory of the Stark Effect on the Donor Levels in 4H Silicon Carbide. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 435-438	0.4	0
94	Optical and morphological features of bulk and homoepitaxial ZnO. <i>Superlattices and Microstructures</i> , <b>2006</b> , 39, 247-256	2.8	10
93	Donor-Acceptor Pair Luminescence of Phosphorus-Aluminum and Nitrogen-Aluminum Pairs in 4H SiC. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 601-604	0.4	
92	Effective-mass approximation for shallow donors in uniaxial indirect band-gap crystals and application to 4H-BiC. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	7
91	Extremely high quantum efficiency of donor-acceptor-pair emission in N-and-B-doped 6H-SiC. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 093108	2.5	59
90	Large-area free-standing GaN substrate grown by hydride vapor phase epitaxy on epitaxial lateral overgrown GaN template. <i>Physica B: Condensed Matter</i> , <b>2006</b> , 371, 133-139	2.8	15
89	Highly homogeneous bulk-like GaN grown by HVPE on MOCVD GaN template. <i>Journal of Crystal Growth</i> , <b>2005</b> , 275, e387-e393	1.6	8
88	Influence of dislocation density on photoluminescence intensity of GaN. <i>Journal of Crystal Growth</i> , <b>2005</b> , 278, 406-410	1.6	4
87	Growth of thick GaN layers with hydride vapour phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2005</b> , 281, 17-316	1.6	51
86	Hot-wall MOCVD grown homoepitaxial GaN layers with intense intrinsic excitonic structure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2005</b> , 202, 739-743	1.6	1
85	High-Quality 2" Bulk-Like Free-Standing GaN Grown by Hydride Vapour Phase Epitaxy on a Si-doped Metal Organic Vapour Phase Epitaxial GaN Template with an Ultra Low Dislocation Density. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, 1181-1185	1.4	34
84	Effective-Mass Theory of Shallow Donors in 4H-SiC. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 511-514	0.4	5
83	SiC and III-Nitride Growth in Hot-Wall CVD Reactor. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 61-66	0.4	7
82	Ionization energies of phosphorus and nitrogen donors and aluminum acceptors in 4H silicon carbide from the donor-acceptor pair emission. <i>Physical Review B</i> , <b>2005</b> , 71,	3.3	40
81	Characterization of crack-free relaxed GaN grown on 2" sapphire. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 073525	2.5	5



80	Characterization of High-Quality Free-Standing GaN Grown by HVPE. <i>Physica Scripta</i> , <b>2004</b> , T114, 18-21	2.6	3
79	Temperature-Dependent Hall Effect Measurements in Low $\Gamma$ -Compensated p-Type 4H-SiC. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 677-680	0.4	10
78	Antisites as Possible Origin of Irradiation Induced Photoluminescence Centers in SiC: A Theoretical Study on Clusters of Antisites and Carbon Interstitials in 4H-SiC. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 443-448	0.4	1
77	Photoluminescence Excitation Spectroscopy on the Donor-Acceptor Pair Luminescence in 4H and 6H SiC. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 585-588	0.4	
76	Homoepitaxial On-Axis Growth of 4H- and 6H-SiC by CVD. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 193-196	0.4	15
75	Hydride vapor-phase epitaxial GaN thick films for quasi-substrate applications: Strain distribution and wafer bending. <i>Journal of Electronic Materials</i> , <b>2004</b> , 33, 389-394	1.9	20
74	Micro-Raman scattering profiling studies on HVPE-grown free-standing GaN. <i>Physica Status Solidi A</i> , <b>2004</b> , 201, 2773-2776		8
73	Direct experimental evidence for unusual effects of hydrogen on the electronic and vibrational properties of GaN <sub>x</sub> P <sub>1-x</sub> alloys: A proof for a general property of dilute nitrides. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	21
72	Defects in SiC. <i>Physica B: Condensed Matter</i> , <b>2003</b> , 340-342, 15-24	2.8	17
71	Anti-site pair in SiC: a model of the DI center. <i>Physica B: Condensed Matter</i> , <b>2003</b> , 340-342, 175-179	2.8	7
70	Fast growth of high quality GaN. <i>Physica Status Solidi A</i> , <b>2003</b> , 200, 13-17		34
69	Photoluminescence Up-Conversion Processes in SiC. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 309-312	0.4	
68	Correlation between the antisite pair and the DI center in SiC. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	66
67	Donor-Acceptor Pair Luminescence in 4H-SiC Doped with Nitrogen and Aluminum. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 321-324	0.4	1
66	Analysis of the sharp donor-acceptor pair luminescence in 4H-SiC doped with nitrogen and aluminum. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	25
65	Optical selection rules for shallow donors in 4H-SiC and ionization energy of the nitrogen donor at the hexagonal site. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	15
64	Excitation spectra of nitrogen bound excitons in 4H- and 6H-SiC. <i>Journal of Applied Physics</i> , <b>2002</b> , 91, 2028-2032	2.5	4
63	Photoconductivity of Lightly-Doped and Semi-Insulating 4H-SiC and the Free Exciton Binding Energy. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 613-616	0.4	4

62	Photoluminescence upconversion in 4H-SiC. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 2547-2549	3.4	3
61	Tunable laser spectroscopy of spin injection in ZnMnSe/ZnCdSe quantum structures. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 2196-2198	3.4	29
60	Photoluminescence line-shape analysis in quantum wells embedded in superlattices. <i>Materials Science and Engineering C</i> , <b>2001</b> , 15, 75-77	8.3	3
59	Intrinsic Photoconductivity of 6H-SiC and the Free-Exciton Binding Energy. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 405-408	0.4	0
58	Resonant sharp hot free-exciton luminescence in 6H- and 4H-SiC due to inhibited exciton-phonon interaction. <i>Physical Review B</i> , <b>2001</b> , 64,	3.3	10
57	Spin Polarization and Injection in ZnMnSe/ZnCdSe Heterostructures. <i>Materials Research Society Symposia Proceedings</i> , <b>2001</b> , 690, F1.7.1		
56	Photoluminescence study of AlAs/GaAs superlattices containing enlarged wells. <i>Thin Solid Films</i> , <b>2000</b> , 364, 224-227	2.2	5
55	High-temperature excitons in GaAs quantum wells embedded in AlAs/GaAs superlattices. <i>Vacuum</i> , <b>2000</b> , 58, 478-484	3.7	5
54	Effect of non-abrupt interfaces in AlAs/GaAs superlattices with embedded GaAs quantum wells. <i>Vacuum</i> , <b>2000</b> , 58, 561-567	3.7	2
53	Vibrational properties and structure of undoped and Al-doped ZnO films deposited by RF magnetron sputtering. <i>Thin Solid Films</i> , <b>2000</b> , 379, 28-36	2.2	209
52	Excitation properties of hydrogen-related photoluminescence in 6H-SiC. <i>Physical Review B</i> , <b>2000</b> , 62, 7162-7168	3.3	7
51	Pseudo-Donors in SiC. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 647-650	0.4	4
50	Metastability of a Hydrogen-related Defect in 6H-SiC. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 651-654	0.4	7
49	B implantation in 6H-SiC: Lattice damage recovery and implant activation upon high-temperature annealing. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1999</b> , 17, 1040		5
48	Thick GaN Layers Grown on A-plane Sapphire Substrates by Hydride Vapour Phase Epitaxy. <i>Physica Scripta</i> , <b>1999</b> , T79, 67	2.6	8
47	Contribution of free-electron recombination to the luminescence spectra of thick GaN films grown by hydride vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>1999</b> , 85, 7888-7892	2.5	31
46	Zeeman spectroscopy of the D1 bound exciton in 3C-SiC and 4H-SiC. <i>Physica B: Condensed Matter</i> , <b>1999</b> , 273-274, 677-680	2.8	6
45	Vibrational studies of copper thiogallate solid solutions. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 57, 102-109	3.1	28

44	Photoluminescence of 4H-SiC: some remarks. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 234-238	3.1	5
43	Photoluminescence excitation spectra of the free exciton emission in 6H-SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 265-269	3.1	4
42	Liquid phase epitaxial growth of SiC. <i>Journal of Crystal Growth</i> , <b>1999</b> , 197, 147-154	1.6	62
41	Photoluminescence of electron-irradiated 4H-SiC. <i>Physical Review B</i> , <b>1999</b> , 59, 8008-8014	3.3	57
40	Properties of the D1 bound exciton in 4H-SiC. <i>Physical Review B</i> , <b>1999</b> , 59, 1956-1963	3.3	72
39	The material quality of CVD-grown SiC using different carbon precursors. <i>Journal of Crystal Growth</i> , <b>1998</b> , 183, 163-174	1.6	28
38	The D1 Exciton in 4H-SiC. <i>Physica Status Solidi (B): Basic Research</i> , <b>1998</b> , 210, 337-340	1.3	4
37	Properties of molecular-beam epitaxy-grown GaNAs from optical spectroscopy. <i>Journal of Applied Physics</i> , <b>1998</b> , 84, 3830-3835	2.5	80
36	6H-SiC Crystallinity Behaviour upon B Implantation Studied by Raman Scattering. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 741-744	0.4	
35	High Growth Rate of SiC by Sublimation Epitaxy. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 143-146	0.4	14
34	Near Band-Gap Emission in V-Implanted and Annealed 4H-SiC. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 497-500	0.4	2
33	Cathodoluminescence of Defect Regions in SiC Epi-Films. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 653-656	0.4	6
32	CVD Growth and Characterisation of SiC Epitaxial Layers on Faces Perpendicular to the (0001) Basal Plane. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 123-126	0.4	16
31	Changes in the Exciton-Related Photoluminescence of 4H- and 6H-SiC Induced by Uniaxial Stress. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 489-492	0.4	0
30	Some Aspects of the Photoluminescence and Raman Spectroscopy of (10-10)- and (11-20)-Oriented 4H and 6H Silicon Carbide. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 469-472	0.4	3
29	Growth and Characterisation of Thick SiC Epilayers by High Temperature CVD. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 103-106	0.4	12
28	Phonon replicas at the M point in 4H-SiC: A theoretical and experimental study. <i>Physical Review B</i> , <b>1998</b> , 58, 13634-13647	3.3	26
27	Direct observation of large-scale nonuniformities in hydride vapor-phase epitaxy-grown gallium nitride by cathodoluminescence. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 3583-3585	3.4	30

26	Bound Exciton Recombination in Electron Irradiated 4H-SiC. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 477-480	0.4	1
25	Exciton Dynamics in Homoepitaxial GaN. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 1275-1278	0.4	7
24	Optical Properties of GaNAs Grown by MBE. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , <b>1998</b> , 3, 1		1
23	Domain Structure of Thick GaN Layers Grown by Hydride Vapor Phase Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , <b>1998</b> , 537, 1		2
22	High quality 4H-SiC grown on various substrate orientations. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 1289-1292	3.5	6
21	Growth of 4H-SiC from liquid phase. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1997</b> , 46, 329-332	3.1	4
20	Optical characterization of MBE-grown GaNAs. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1997</b> , 50, 153-156	3.1	2
19	Exciton dynamics in homoepitaxial GaN. <i>Solid State Communications</i> , <b>1997</b> , 104, 205-209	1.6	13
18	Growth of SiC by Hot-Wall CVD and HTCVD. <i>Physica Status Solidi (B): Basic Research</i> , <b>1997</b> , 202, 321-334	1.3	115
17	High-resolution x-ray analysis of InGaN/GaN superlattices grown on sapphire substrates with GaN layers. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 3390-3392	3.4	25
16	Raman study of complexation in aqueous solutions of magnesium acetate. <i>Journal of Molecular Structure</i> , <b>1996</b> , 377, 13-17	3.4	23
15	Characterization of the ternary compounds AgGaTe <sub>2</sub> and AgGa <sub>5</sub> Te <sub>8</sub> . <i>Journal of Materials Science</i> , <b>1996</b> , 31, 3315-3319	4.3	24
14	Ga-bound excitons in 3C-, 4H-, and 6H-SiC. <i>Physical Review B</i> , <b>1996</b> , 53, 13503-13506	3.3	22
13	Nitrogen doping concentration as determined by photoluminescence in 4H- and 6H-SiC. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 3504-3508	2.5	80
12	High temperature chemical vapor deposition of SiC. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 1456-1458	3.4	101
11	The growth of V <sub>2</sub> O <sub>5</sub> flash-evaporated films. <i>Journal of Materials Science Letters</i> , <b>1995</b> , 14, 934-936		24
10	The influence of the substrate material on the growth of V <sub>2</sub> O <sub>5</sub> flash-evaporated films. <i>Applied Surface Science</i> , <b>1995</b> , 90, 389-391	6.7	60
9	Vibrational modifications on lithium intercalation in V <sub>2</sub> O <sub>5</sub> films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1995</b> , 33, 168-172	3.1	32

8	Raman and IR study of cobalt acetate dihydrate. <i>Journal of Molecular Structure</i> , <b>1995</b> , 354, 119-125	3.4	38
7	The growth and electrochemical properties of V6O13 flash-evaporated films. <i>Solid State Ionics</i> , <b>1995</b> , 76, 133-141	3.3	17
6	Ga Bound Excitons in 6H-SiC. <i>Materials Science Forum</i> , <b>1995</b> , 196-201, 91-96	0.4	
5	Spectral Behavior of Zero-Bias Photocurrent at Low Temperature in Bulk Semi-Insulating GaAs : Cr. <i>Journal of the Electrochemical Society</i> , <b>1994</b> , 141, 2533-2536	3.9	3
4	Optical and Electrical Properties of Ga <sub>2</sub> Te <sub>3</sub> Crystals. <i>Physica Status Solidi A</i> , <b>1994</b> , 145, 207-215		14
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